

FIG. 1

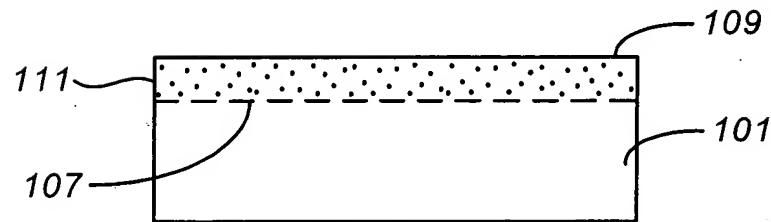


FIG. 2

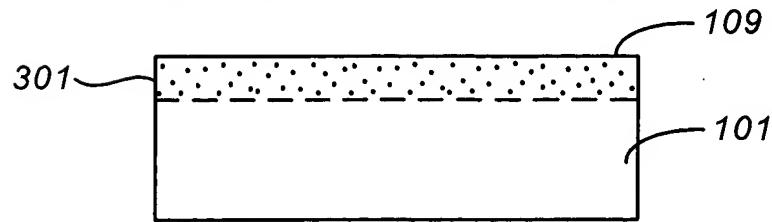
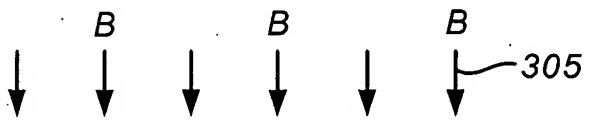


FIG. 3

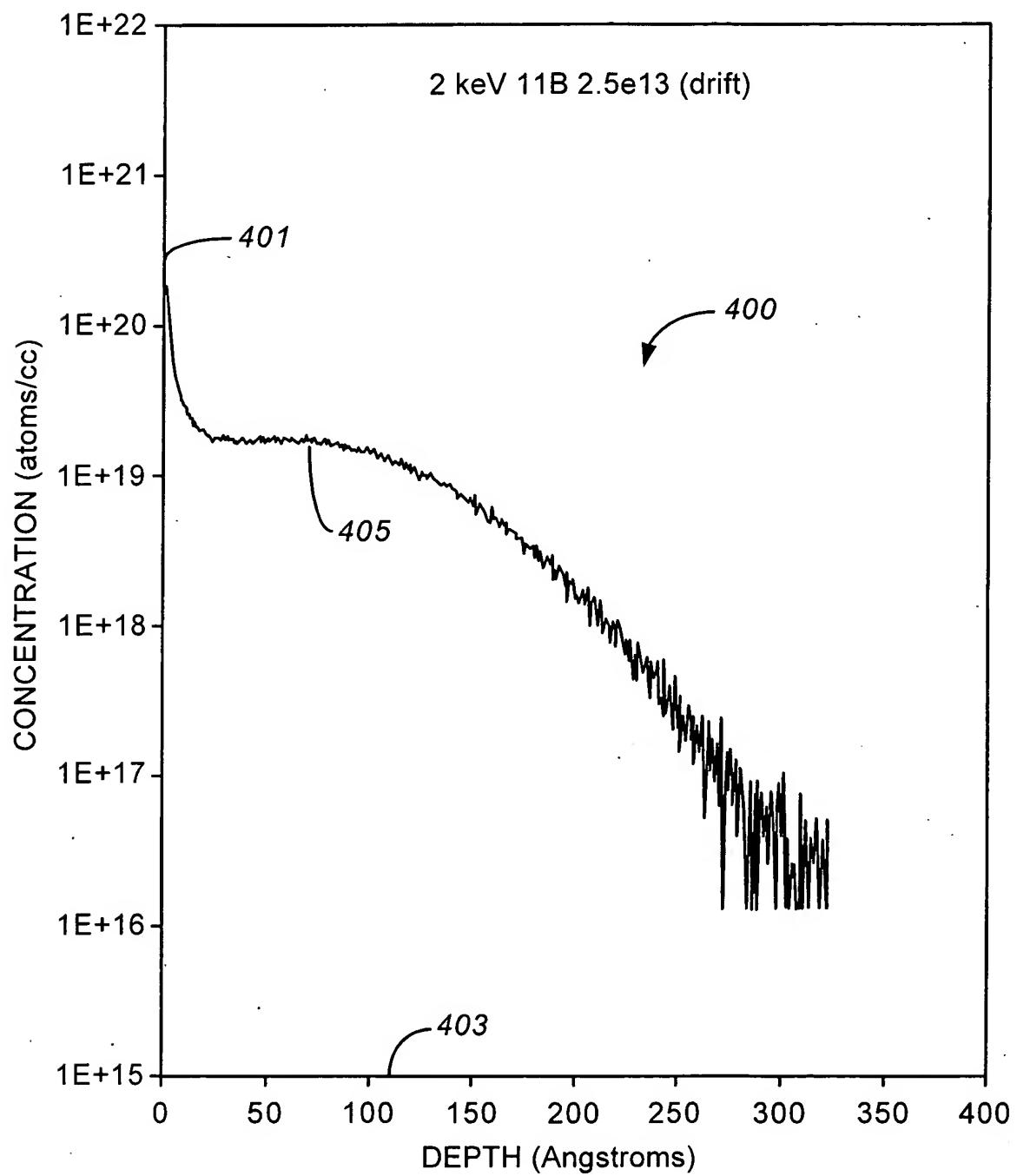


FIG. 4

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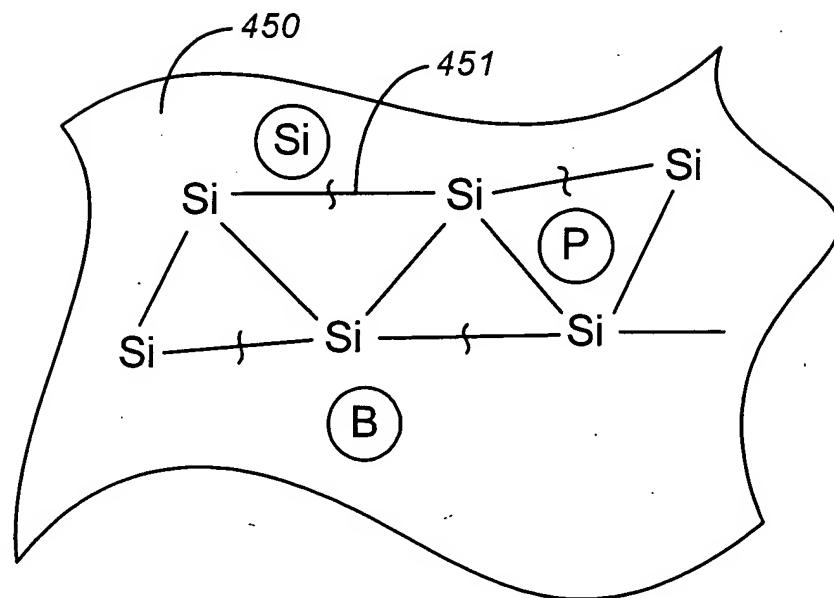


FIG. 4A

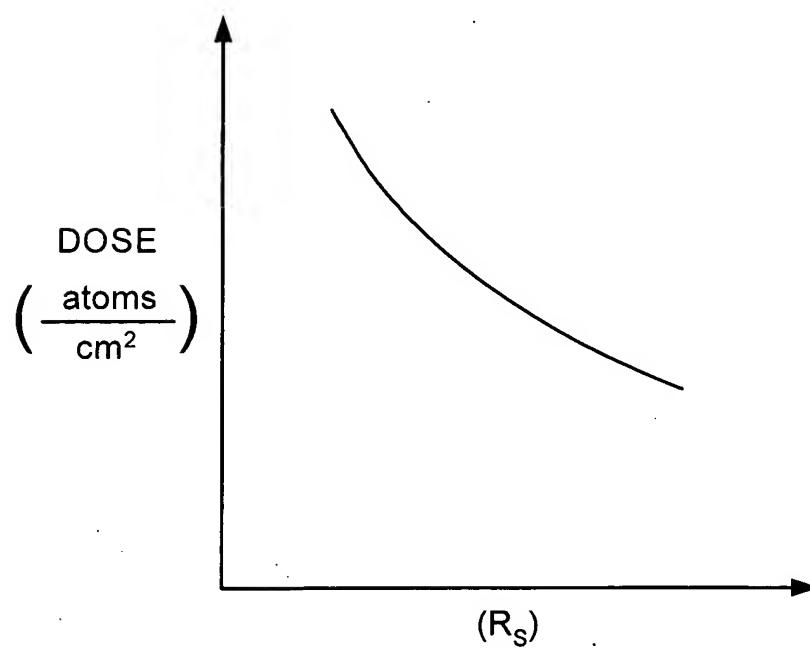


FIG. 5

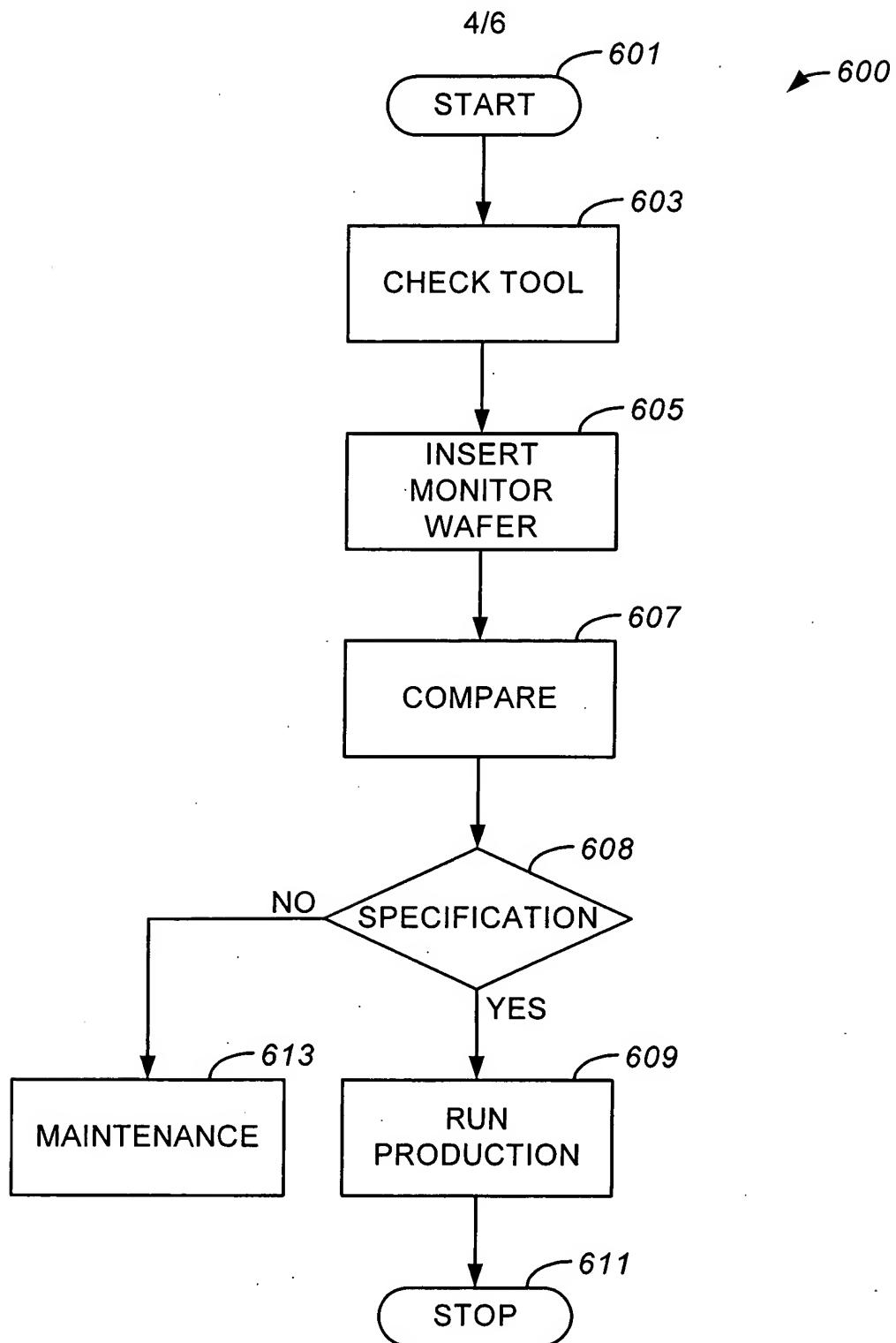


FIG. 6

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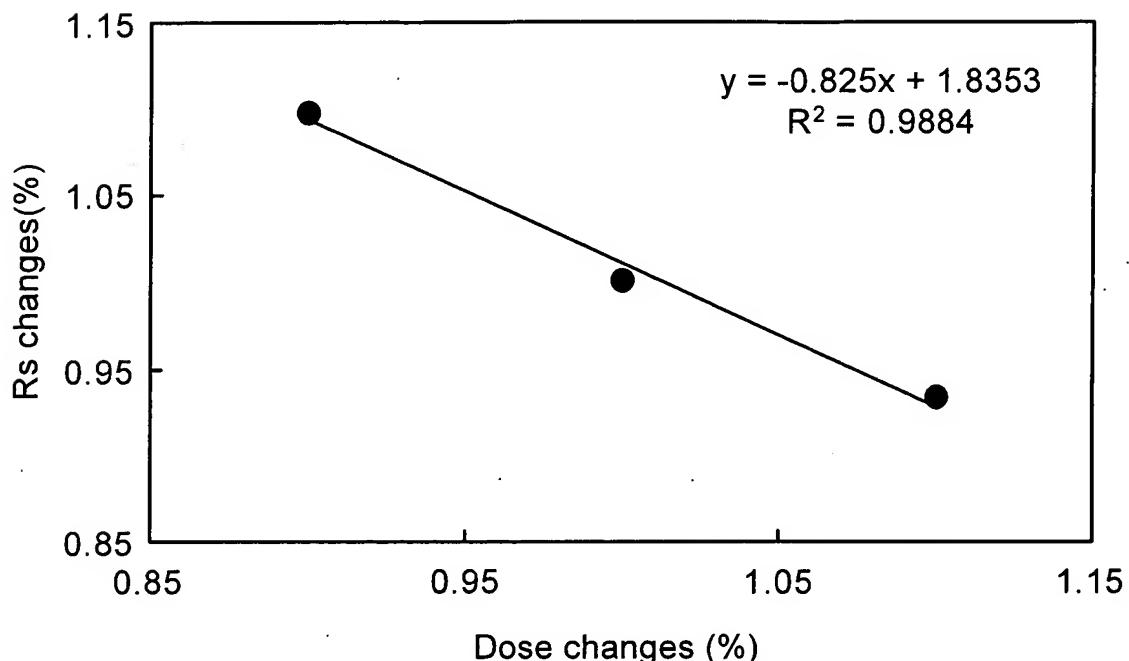


FIG. 7

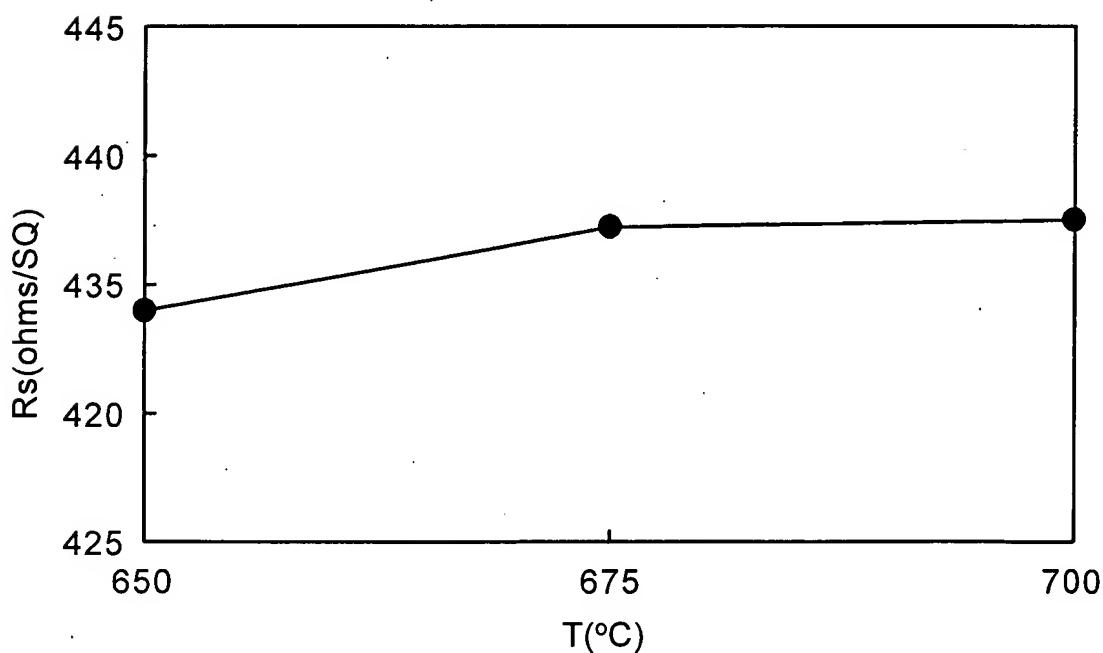


FIG. 8

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Table 1 The effect of silicon implantation on Boron activation.
Implantation conditions: Silicon/20KeV/1E15 before Boron/2KeV/4E14;
annealing conditions: 700°C, 30 seconds, N₂ as annealing ambient

	Implantation	Annealing	Rs/Uniformity(%)
Implanted with both Si and B	Si/20K/1E15/T07+ B/2K40E4/T00	T0700RTA30S	442.72/0.329%
Implanted with B only	B/2K/40E4/T00		7940.3/1.352%

FIG. 9